

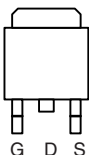
N-Channel 60-V (D-S), 175 °C MOSFET

PRODUCT SUMMARY		
$V_{(BR)DSS}$ (V)	$r_{DS(on)}$ (Ω)	I_D (A)
60	0.0093 at $V_{GS} = 10$ V	90
	0.0135 at $V_{GS} = 4.5$ V	62

FEATURES

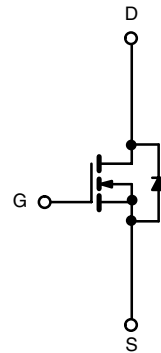
- TrenchFET[®] Power MOSFET
- 175 °C Junction Temperature


 Available
RoHS*
 COMPLIANT

TO-263


Top View

DRAIN connected to TAB

Ordering Information: SUM75N06-09L-E3 (Lead (Pb)-free)


N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 175$ °C)	I_D	$T_C = 25$ °C	90
		$T_C = 100$ °C	53
Pulsed Drain Current	I_{DM}	160	A
Avalanche Current	I_{AR}	50	
Repetitive Avalanche Energy ^a	E_{AR}	125	mJ
Power Dissipation	P_D	$T_C = 25$ °C	125 ^b
		$T_A = 25$ °C ^c	3.75 ^c
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Limit	Unit
Junction-to-Ambient	R_{thJA}	40	°C/W
Junction-to-Case	R_{thJC}	1.2	

Notes:

- Duty cycle ≤ 1 %.
- See SOA curve for voltage derating.
- When Mounted on 1" square PCB (FR-4 material).

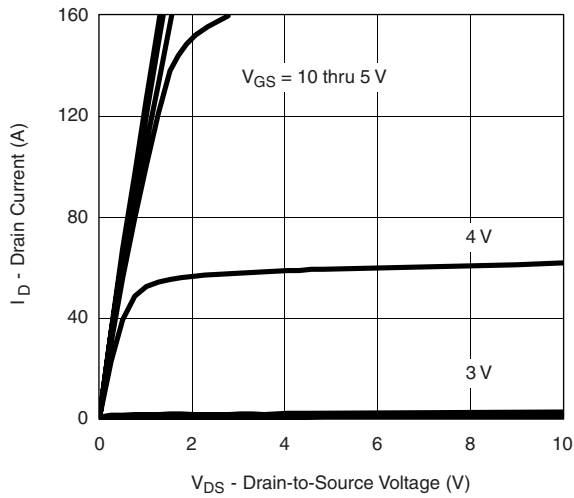
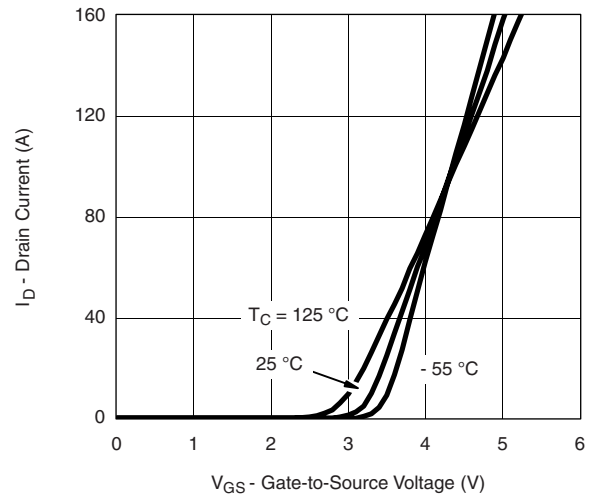
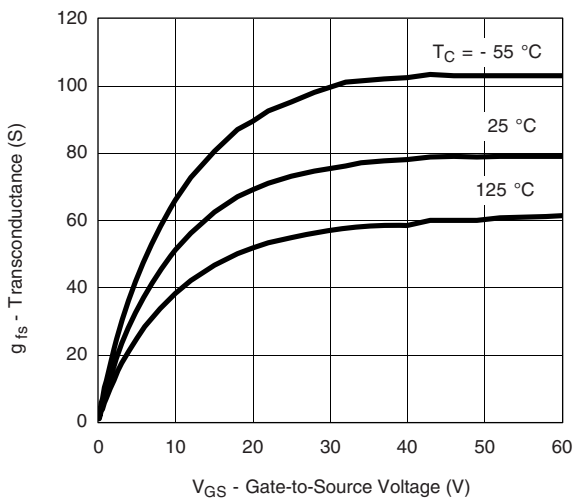
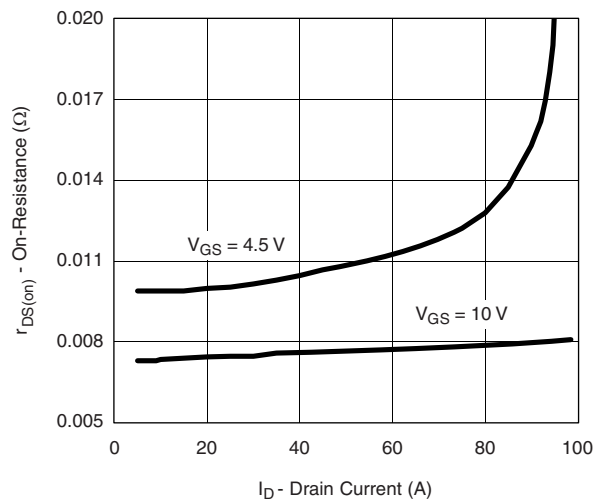
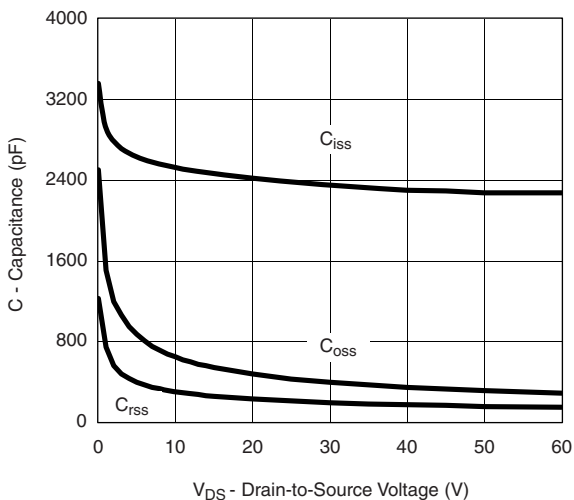
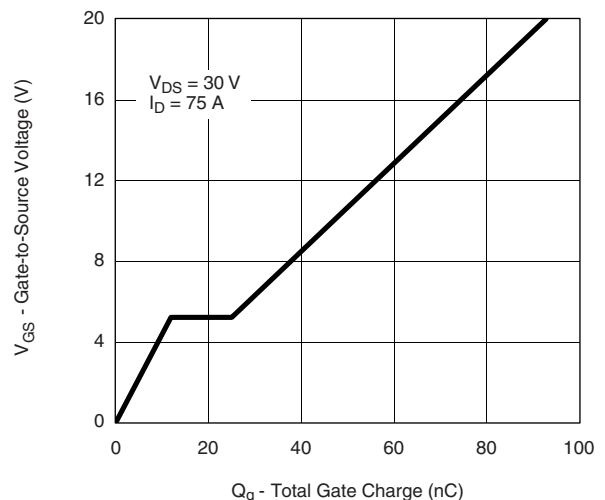
* Pb containing terminations are not RoHS compliant, exemptions may apply.

MOSFET SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	60			V
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1	2	3	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$			50	
		$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}, T_J = 175\text{ }^\circ\text{C}$			150	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = 5\text{ V}, V_{GS} = 10\text{ V}$	75			A
Drain-Source On-State Resistance ^a	$r_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 30\text{ A}$		0.0075	0.0093	Ω
		$V_{GS} = 10\text{ V}, I_D = 30\text{ A}, T_J = 125\text{ }^\circ\text{C}$			0.0163	
		$V_{GS} = 10\text{ V}, I_D = 30\text{ A}, T_J = 175\text{ }^\circ\text{C}$			0.024	
		$V_{GS} = 4.5\text{ V}, I_D = 30\text{ A}$		0.0105	0.0135	
		$V_{GS} = 4.5\text{ V}, I_D = 30\text{ A}, T_J = 125\text{ }^\circ\text{C}$			0.0224	
$V_{GS} = 4.5\text{ V}, I_D = 30\text{ A}, T_J = 175\text{ }^\circ\text{C}$			0.030			
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 30\text{ A}$	25	75		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		2400		pF
Output Capacitance	C_{oss}			430		
Reverse Transfer Capacitance	C_{rss}			210		
Total Gate Charge ^c	Q_g	$V_{DS} = 30\text{ V}, V_{GS} = 10\text{ V}, I_D = 90\text{ A}$		47	75	nC
Gate-Source Charge ^c	Q_{gs}			12		
Gate-Drain Charge ^c	Q_{gd}			13		
Turn-On Delay Time ^c	$t_{d(on)}$	$V_{DD} = 30\text{ V}, R_L = 0.4\text{ }\Omega$ $I_D \cong 90\text{ A}, V_{GEN} = 10\text{ V}, R_G = 2.5\text{ }\Omega$		7	12	ns
Rise Time ^c	t_r			30	50	
Turn-Off Delay Time ^c	$t_{d(off)}$			25	40	
Fall Time ^c	t_f			12	20	
Source-Drain Diode Ratings and Characteristics $T_C = 25\text{ }^\circ\text{C}$^b						
Continuous Current	I_S				90	A
Pulsed Current	I_{SM}			160	180	
Forward Voltage ^a	V_{SD}	$I_F = 90\text{ A}, V_{GS} = 0\text{ V}$			1.4	V
Reverse Recovery Time	t_{rr}	$I_F = 50\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		40	80	ns
Peak Reverse Recovery Current	$I_{RM(REC)}$			2	4	A
Reverse Recovery Charge	Q_{rr}			0.040	0.16	μC

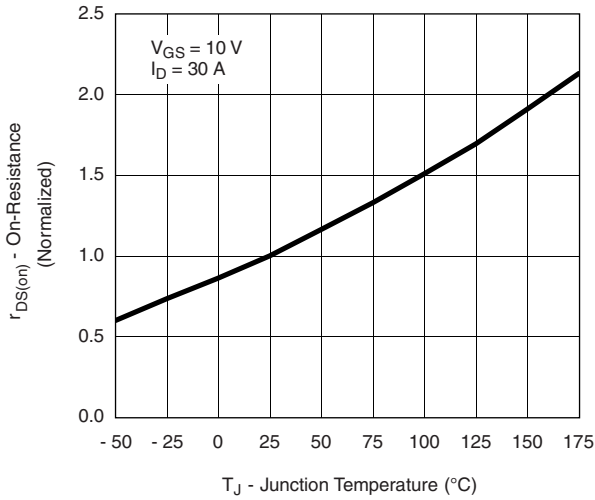
Notes:

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

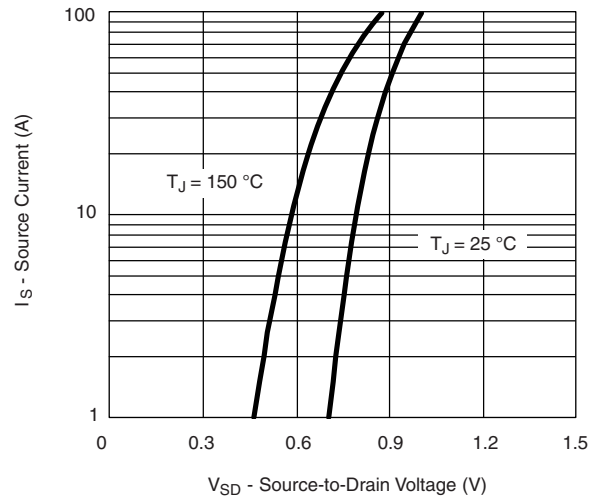
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

Output Characteristics

Transfer Characteristics

Transconductance

On-Resistance vs. Drain Current

Capacitance

Gate Charge

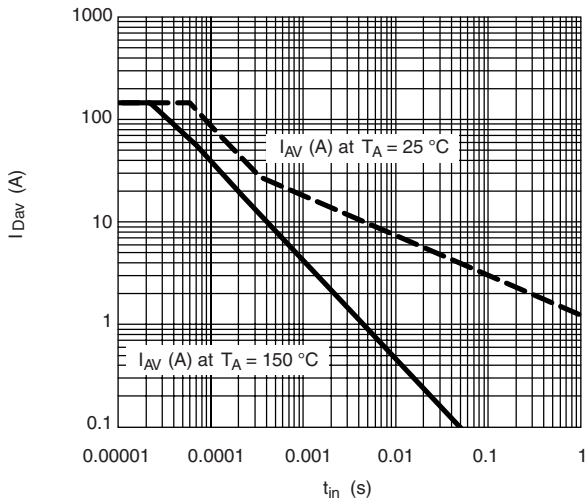
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



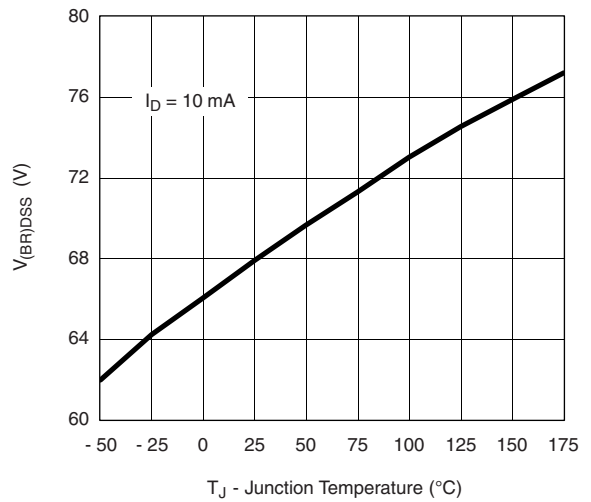
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage

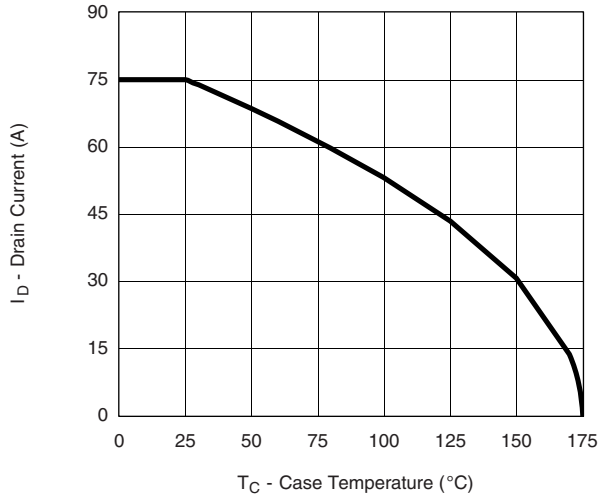


Avalanche Current vs. Time

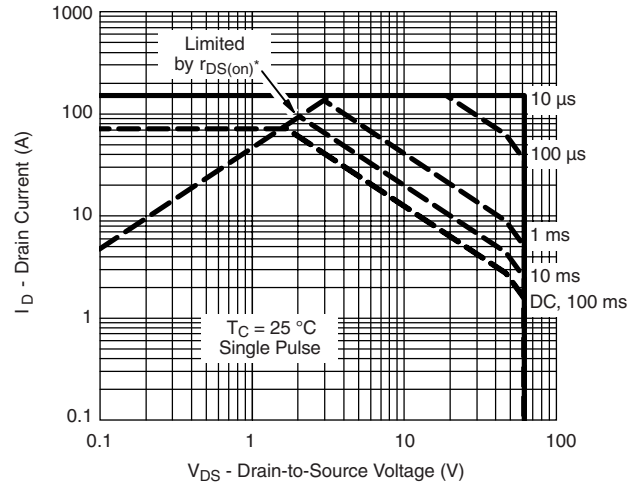


Drain Source Breakdown vs. Junction Temperature

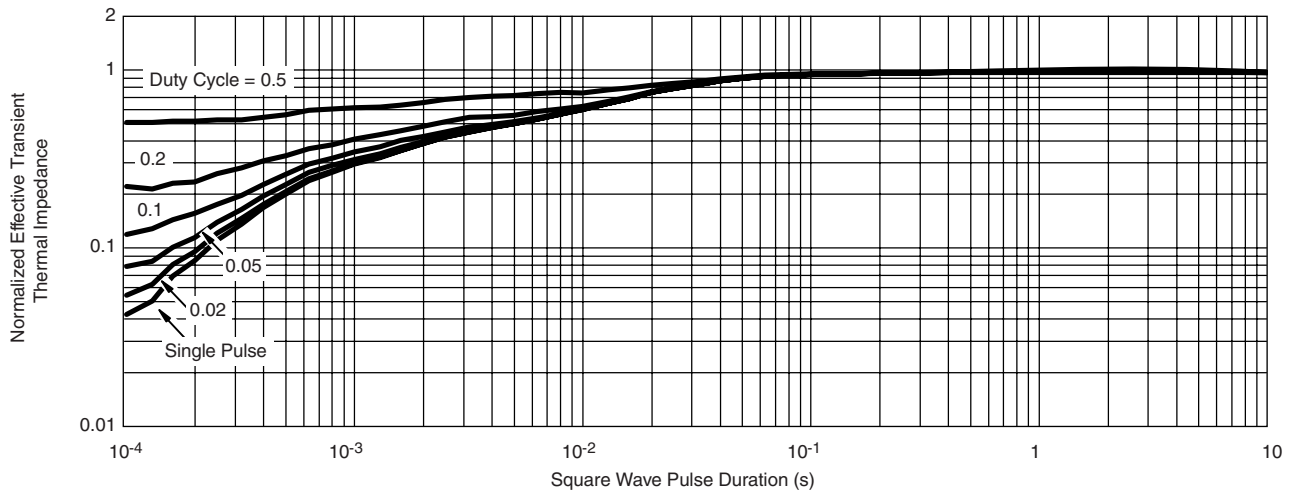
THERMAL RATINGS



Maximum Avalanche Drain Current vs. Case Temperature



Safe Operating Area, Junction-to-Case



Normalized Thermal Transient Impedance, Junction-to-Case

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